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Silicon Epitaxial Planar Pin Diode for High Frequency Switching



ADE-208-1508A (Z)

Rev.1 Jun. 2002

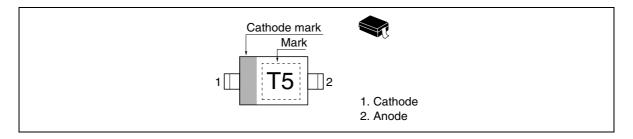
Features

- Low capacitance.(C = 0.45 pF max)
- Low forward resistance. (rf = $1.8 \Omega \text{ max}$)
- Ultra small Resin Package (URP) is suitable for surface mount design.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HVU145 | Τ5 | URP |

Pin Arrangement



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Value | Unit |
|----------------------|----------------|-------------|------|
| Reverse voltage | V _R | 60 | V |
| Forward current | I _F | 50 | mA |
| Power dissipation | Pd | 150 | mW |
| Junction temperature | Tj | 125 | °C |
| Storage temperature | Tstg | –55 to +125 | °C |

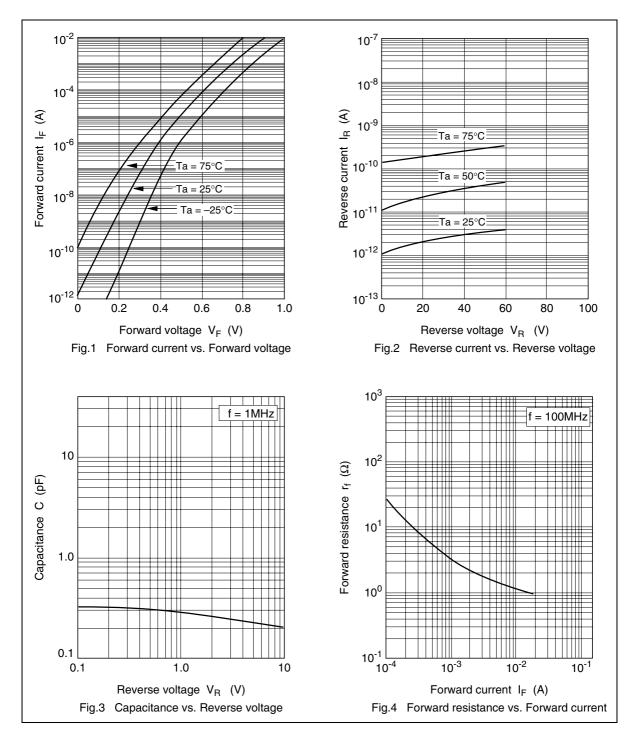
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

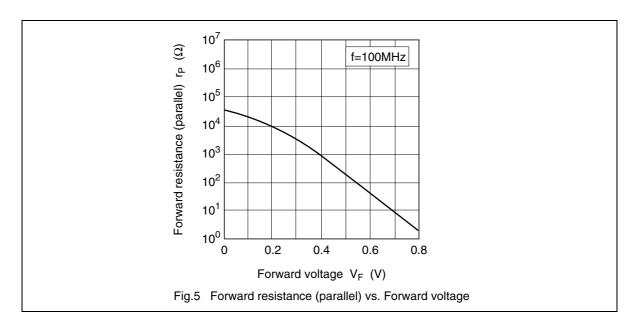
| Item | Symbol | Min | Тур | Max | Unit | Test Condition |
|--------------------|----------------|-----|-----|------|------|--|
| Reverse current | I _R | _ | _ | 100 | nA | V _R = 60 V |
| Forward voltage | V _F | _ | _ | 0.9 | V | I _F = 2 mA |
| Capacitance | С | _ | _ | 0.45 | pF | $V_{_{\mathrm{R}}} = 1 \text{ V}, \text{ f} = 1 \text{ MHz}$ |
| Forward resistance | r, | _ | _ | 1.8 | Ω | I _F = 10 mA, f = 100 MHz |
| ESD-Capability *1 | _ | 100 | — | — | V | C = 200 pF, R = 0 Ω , Both forward and reverse direction 1 pulse. |

Note : 1. Failure criterion ; $I_{_{\rm R}} \ge 100$ nA at $V_{_{\rm R}} = 60$ V

Main Characteristic

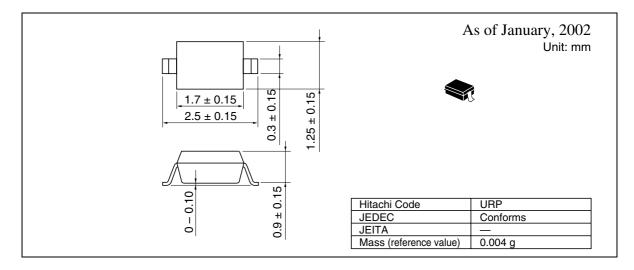


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Package Dimensions





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